

Dual P-Channel 30 V (D-S) MOSFET

PRODUCT SUMMARY						
V _{DS} (V)	R _{DS(on)} (mΩ)(Typ.)	I _D (A) ^a	Q _g (Typ.)			
- 30	19 at V _{GS} = - 10 V	- 8.8	18 nC			
- 30	29 at V _{GS} = - 4.5 V	- 0.0				

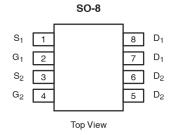
FEATURES

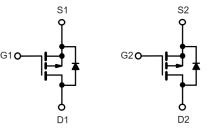
- DT-Trench Power MOSFET
- 100 % Rg and UIS Tested
- Surface mount package

RoHS

APPLICATIONS

- Battery Switch
- Load switch
- Power management





P1-Channel MOSFET

P2-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	LIMIT	UNIT			
Drain-Source Voltage	V _{DS}	- 30				
Gate-Source Voltage	V _{GS}	± 20	V			
Continuous Drain Current /T 150 °C)2	T _C = 25 °C		- 8.8	А		
Continuous Drain Current (T _J = 150 °C) ^a	T _C = 100 °C	I _D	- 5.4			
Pulsed Drain Current ^b	I _{DM}	- 36				
Single Avalanche Energy	E _{AS}	32	mJ			
Maximum Dawar Dissinations	T _C = 25 °C	В	5.5	W		
Maximum Power Dissipation ^c	T _C = 100 °C	$\overline{}$ P_{D}	2.2			
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to +150	°C		

THERMAL RESISTANCE RATINGS					
PARAMETER	SYMBOL	LIMIT	UNIT		
Junction-to-Ambient (PCB Mount) ^d	R _{thJA}	85	°C/W		
Junction-to-Case (Drain)	R _{thJC}	22.7	C/vv		

Notes

- a. Calculated continuous current based on maximum allowablejunction temperature.
- b. Repetitive rating; pulse width limited by max. junction temperature.
- c. Pd is based on max. junction temperature, using junction-case thermal resistance.
- d. The value of R_{0JA} is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper,in a still air environment with Ta=25 °C.



PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static				•			
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = -250 \ \mu\text{A}$	- 30	-	-	V	
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 1	-	- 3	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 10 \text{ V}$	-	-	± 100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = -30 \text{ V}, V_{GS} = 0 \text{ V}$	-	-	- 1	μΑ	
Drain-Source On-State Resistance a	R _{DS(on)}	V _{GS} = - 10 V, I _D = - 5 A	-	19	25	mΩ	
Drain-Source On-State Resistance	TIDS(on)	$V_{GS} = -4.5 \text{ V}, I_D = -5 \text{ A}$	-	29	35		
Forward Transconductance ^a	g_{fs} $V_{DS} = -10 \text{ V}, I_D = -5 \text{ A}$		-	18	-	S	
Dynamic ^b							
Input Capacitance	C _{iss}		-	1140	-	pF	
Output Capacitance	C _{oss}	V _{GS} = 0 V, V _{DS} = - 15 V, f = 1MHz	-	143	-		
Reverse Transfer Capacitance	C _{rss}		-	129	-		
Total Gate Charge ^c	Qg		-	18	-	nC	
Gate-Source Charge ^c	Q _{gs}	$V_{DS} = -15 \text{ V}, V_{GS} = -10 \text{ V}, I_D = -5 \text{ A}$	-	3.5	-		
Gate-Drain Charge ^c	Q_{gd}		-	5	-		
Gate Resistance	R _g	f = 1 MHz	-	4.3	-	Ω	
Turn-On Delay Time ^c	t _{d(on)}		-	10	-	ns ns	
Rise Time °	t _r	$V_{DS} = -15 \text{ V}, I_{D} = -5 \text{ A},$	-	7	-		
Turn-Off Delay Time ^c	t _{d(off)}	$V_{GS} = -10 \text{ V}, R_g = 3 \Omega$	-	30	-		
Fall Time ^c	t _f		-	11	-		
Drain-Source Body Diode Ratings ar	nd Characteri	stics ^b (T _C = 25 °C)					
Continuous Source Current	I _S	T _C = 25 °C	-	-	- 8.8	Α	
Pulsed Current	I _{SM}		_	-	- 36	Α	
Forward Voltage ^a	V _{SD}	I _S = - 1 A, V _{GS} = 0 V	-	-	- 1.2	V	
Reverse Recovery Time	t _{rr}	L 5 A di/dt 100 A/:	-	12	-	ns	
Reverse Recovery Charge	Q _{rr}	$I_S = -5 \text{ A, di/dt} = 100 \text{ A/}\mu\text{s}$	-	25	-	nC	

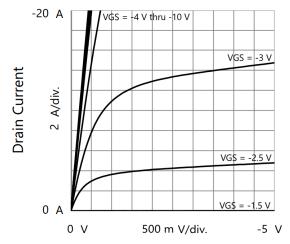
Notes

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

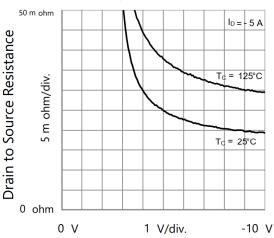
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



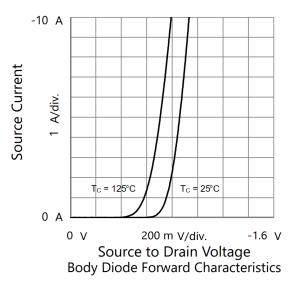
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

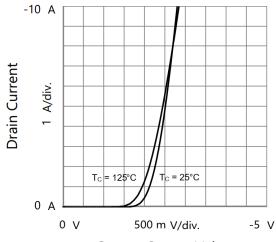


Drain to Source Voltage Output Characteristics

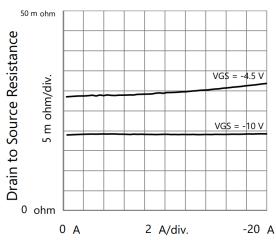


Gate to Source Voltage
Drain to Source Resistance vs. Gate to Source Voltage

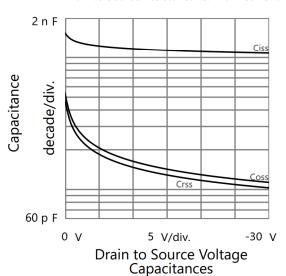




Gate to Source Voltage Transfer Characteristics



Drain Current
Drain to Source Resistance vs. Drain Current

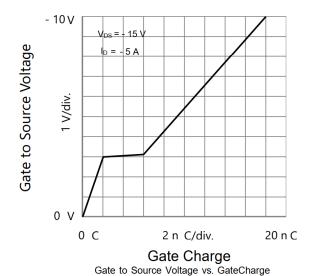


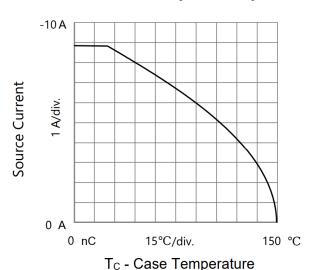
- 100 V

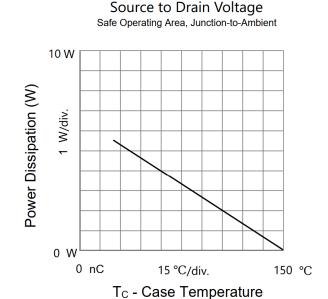




TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)







decade/div.

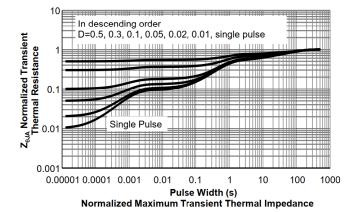
- 100 A

decade/div.

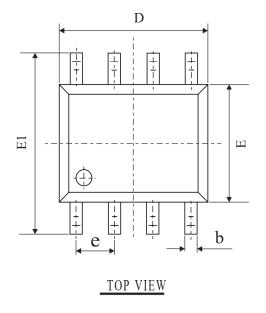
- 0.01 A

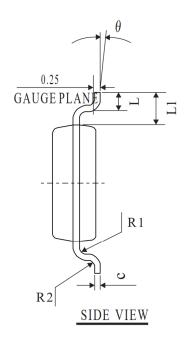
- 0.01 V

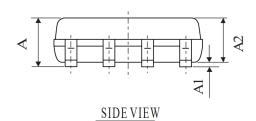
Source Current



SOP-8 PACKAGE OUTLINE







COMMON DIMENSIONS (UNITS OF MEASURE=MILLIMETER)

SYMBOL	MIN	TYP	MAX
Α	1.30	1.60	1.85
A1	0.03	0.15	0.28
A2	1.20	1.45	1.70
b	0.26	0.40	0.54
С	0.132	0.203	0.273
D	4.50	4.90	5.30
Е	3.50	3.00	4.30
E1	5.50	6.00	6.50
L	0.30	0.70	1.10
θ	2°	4°	6°
L1	1.04REF		
e	1.27BSC		
R1	0.07TYP		
R2	0.07TYP		

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